



# UFHV SERIES

2 to 4kV, 350 to 500mA, 75nS  
Axial Lead Power Diodes



## Features

- Miniature Package
- Glass Passivated Junctions

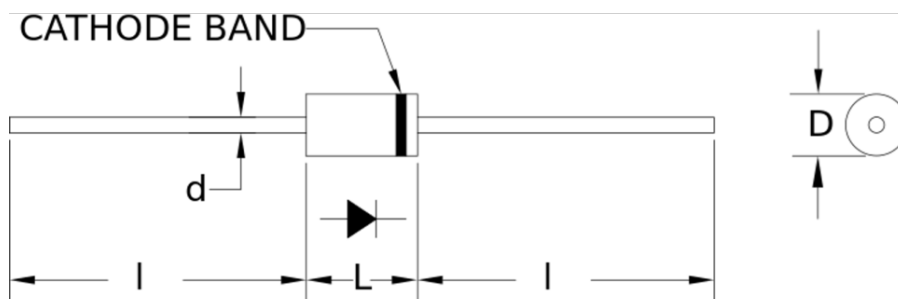
## Specifications<sup>1</sup>

Part Number	V <sub>RRM</sub> V	I <sub>FAVM</sub> mA	V <sub>F</sub> V	I <sub>R</sub> μA	I <sub>FSM</sub> A	C <sub>J</sub> pF	T <sub>RR</sub> nS	L in.	D in.	d in.	I in.
UFHV2K	2000	550	3.0	5	30	12	75	0.200	0.100	0.034	1.000
UFHV3K	3000	400	4.1	5	30	8	75	0.200	0.100	0.034	1.000
UFHV4K	4000	350	5.5	5	30	6	75	0.200	0.100	0.034	1.000

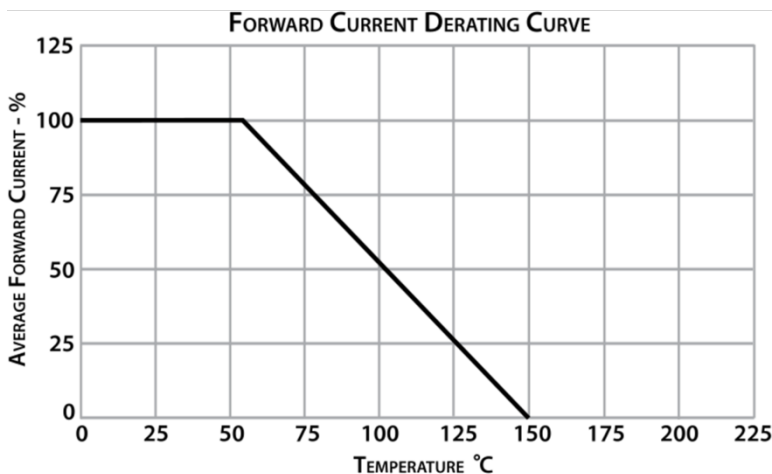
Temperature °C	
Storage Temperature	-55 to 175
Operating Temperature	-55 to 150
Maximum Junction Temperature	150

<sup>1</sup>125°C ambient temperature unless stated otherwise.

## Drawings



Dimensions in inches, tolerances ±0.020 except as noted





## Specification Definitions

	Specifications	Conditions
<b>V<sub>RRM</sub></b>	Maximum Repetitive Reverse Voltage	-
<b>I<sub>FAVM</sub></b>	Maximum Average Forward Current	At T <sub>A</sub> = 55°C
<b>V<sub>F</sub></b>	Maximum Forward Voltage Drop	At I <sub>FAVM</sub>
<b>I<sub>R</sub></b>	Maximum Leakage Current	At V <sub>RRM</sub>
<b>I<sub>FSM</sub></b>	Maximum Surge Current	At 8.3mS, Single Half Sine
<b>C<sub>J</sub></b>	Typical Junction Capacitance	At V <sub>R</sub> = 0VDC, f = 1MHz
<b>T<sub>RR</sub></b>	Maximum Reverse Recovery Time	I <sub>F</sub> = 0.5 I <sub>FAVM</sub> ; I <sub>R</sub> = -I <sub>FAVM</sub> ; I <sub>RR</sub> = -0.25 I <sub>FAVM</sub>

Note: Specifications subject to change without notice. Photo is representation only.

